



Atty Docket No.: RBS2.P031

PATENT

IN THE UNITED STATES PATENT OFFICE

2187  
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**In Re Patent Application of:**

First Named Inventor: Garrett, Jr., Billy

Application No.: 09/837,307

Filed: 4/17/2001

Title: MECHANISM FOR ENABLING FULL DATA BUS  
UTILIZATION WITHOUT INCREASING DATA  
GRANULARITY

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Examiner: Dinh, Ngoc V.

Art Unit: 2187

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria VA 22313-1450 on July 25, 2005

Kyle S. Okada

(Name of Person Mailing Correspondence)

Kyle S. Okada  
Signature

July 25, 2005  
Date

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

Sir:

Enclosed is an Information Disclosure Citation Form 1449/PTO together with a copy of each reference cited therein, excluding U.S. Patents and Published U.S. Patent Applications. It is respectfully requested that the cited references be considered and that the enclosed copy of the Form 1449/PTO be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant.

This Information Disclosure Statement is being submitted pursuant to 37 CFR 1.97(b). No fee is believed to be due.

Pursuant to 37 CFR 1.97(h), the submission of this Information Disclosure Statement is not to be construed as an admission that the information cited in this statement is material to patentability.

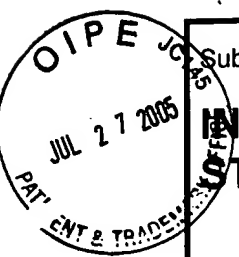
The Commissioner is hereby authorized to charge any fees which may be required in connection with this submission to Deposit Account No. 501914.

Respectfully submitted,

SHEMWELL GREGORY & COURTNEY LLP

Date July 25, 2005

Charles E. Shemwell, Reg. No. 40,171  
Tel. 408-236-6645



Substitute for Form 1449/PTO

# **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

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<b>Filed</b>	4/17/2001
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<b>Examiner</b>	Dinh, Ngoc V.
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U.S. Patent Documents					
Examiner Initials*	US Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication	Relevant Pages, Columns, Lines
	Number	Kind			
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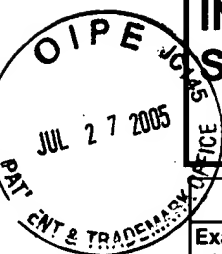
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**Foreign Patent Documents**

Examiner Initials*	Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication	Relevant Pages, Columns, Lines	Trans- lation
	Number	Kind				
	EP0887737	B1		1/22/2003		
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**Non Patent Literature Documents**

Examiner Initials	Name of Author, Title of Item, Date, Page(s), Volume-Issue Number(s), Publisher, City and/or Country where Published	Trans- lation
	C. Yoo et al., "A 1.8V 700 Mb/s/pin 512Mb DDR-II SDRAM with On-Die Termination and Off-Chip Driver Calibration, IEEE International Solid-State Circuits Conference ISSCC 2003/Session 17/SRAM and DRAM/ Paper 17.7, pp. 312-313 and 496, plus Visuals Supplement on pp. 250-251 and 535	
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	S. Takase and N.i Kushiya, "WP 24.1 A 1.6GB/s DRAM with Flexible Mapping Redundancy Technique and Additional Refresh Scheme," IEEE Journal of Solid State Circuits, Vol. 34, No. 11, November 1999, pp. 1600-1606	
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	Samsung Electronics, "SDRAM Device Operations," 41 pages, date unknown.	
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